

# New Jersey Semi-Conductor Products, Inc.

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## Silicon PNP Power Transistor

## 2SA1063

### DESCRIPTION

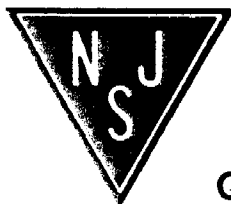
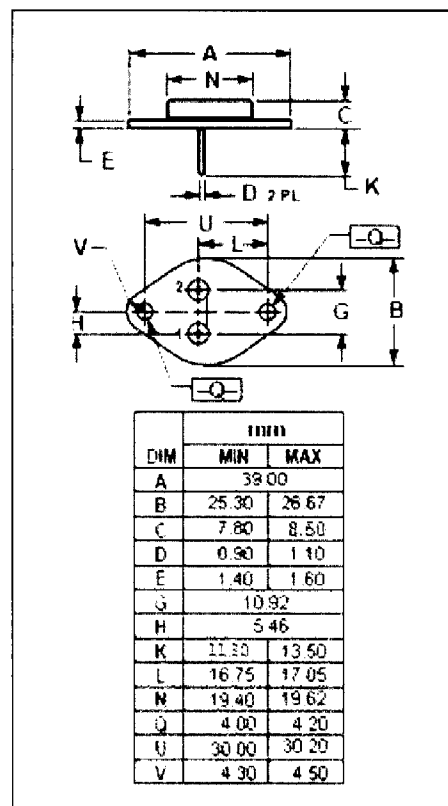
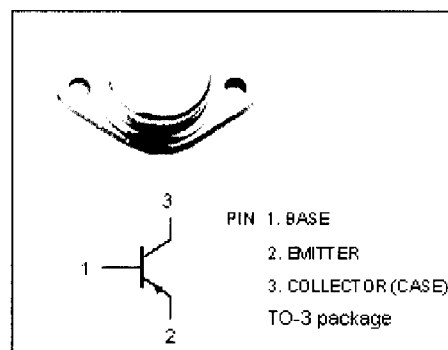
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -120V(\text{Min.})$
- Good Linearity of  $h_{FE}$
- Wide Area of Safe Operation
- Complement to Type 2SC2487

### APPLICATIONS

- Designed for AF amplifier, high power amplifier applications.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-150	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-6	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors**

**Silicon PNP Power Transistor****2SA1063****ELECTRICAL CHARACTERISTICS**T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = 0	-120			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.6A			-2.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -6A; V <sub>CE</sub> = -5V			-2.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -120V; I <sub>E</sub> = 0			-1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-2	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> = -5V	40		280	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -6A; V <sub>CE</sub> = -5V	20			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V		50		MHz

◆ **h<sub>FE-2</sub> Classifications**

R	Q	P	O
40-80	60-120	90-180	140-280